



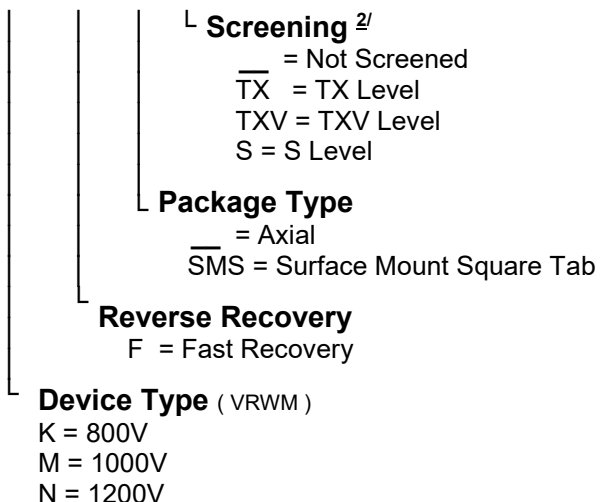
Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638
 Phone: (562) 404-4474 * Fax: (562) 404-1773
 ssdi@ssdi-power.com * www.ssdi-power.com

Designer's Data Sheet

Part Number/Ordering Information ^{1/}

SPR2



SPR2KF thru SPR2NF

REVERSE TRANSIENT RATED

2 AMP
FAST RECTIFIER
 800 - 1200 Volts
 200 nsec

FEATURES:

- Fast Reverse Recovery Time: 200 nsec Max
- PIV to 1200 Volts
- Reverse Transient Rated: 1 Amp (Typ 1200 Wpk)
- Hermetically Sealed
- For High Efficiency Applications
- Available in Axial and Surface Mount Versions
- Metallurgically Bonded
- Solid Silver Leads for High Thermal Conductivity
- TX, TXV, and S-Level Screening Available ^{2/}

MAXIMUM RATINGS ^{3/}

RATING		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage DC Blocking Voltage	SPR2K	V_{RRM}	800	V
	SPR2M	V_{RWM}	1000	
	SPR2N	V_R	1200	
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, $T_C = 25^\circ\text{C}$)		I_O	2	A
Peak Surge Current (8.3ms pulse, half sine wave superimposed on I_O , allow junction to reach equilibrium between pulses, $T_A = 25^\circ\text{C}$)		I_{FSM}	60	A
Operating & Storage Temperature		T_{OP} and T_{STG}	-65 to +175	$^\circ\text{C}$
Maximum Thermal Resistance	Junction to Leads, L=3/8" (Axial)	$R_{\theta JL}$	38	$^\circ\text{C/W}$
	Junction to End Tab (SMS)	$R_{\theta JE}$	7.0	

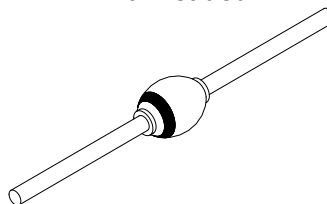
NOTES:

^{1/} For Ordering Information, Price, and Availability- Contact Factory.

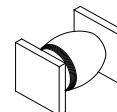
^{2/} Screening Based on MIL-PRF-19500. Screening Flows Available on Request.

^{3/} Unless Otherwise Specified, All Electrical Characteristics @25°C.

Axial Leaded



SMS



NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RC0134B

DOCX

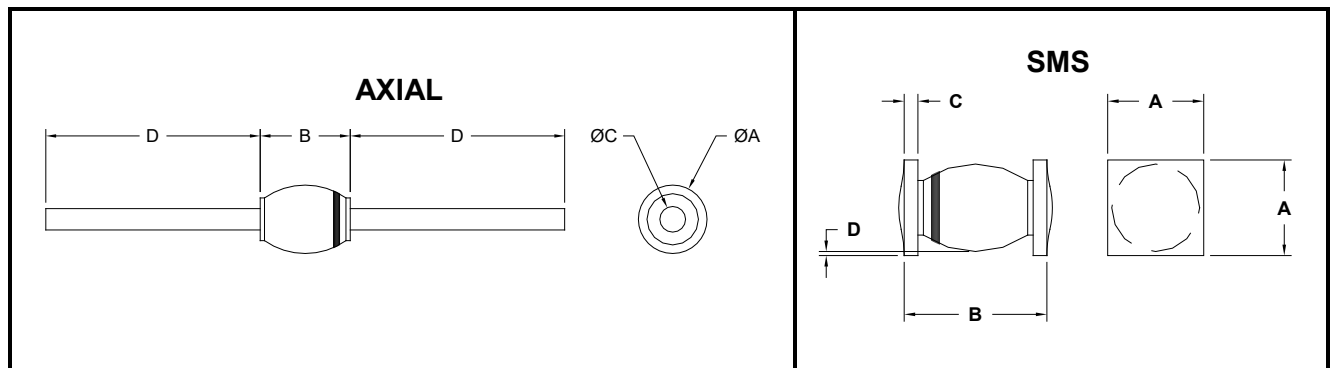


Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638
Phone: (562) 404-4474 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

SPR2KF thru SPR2NF

CHARACTERISTICS	SYMBOL	MAX	UNIT
Instantaneous Forward Voltage Drop ($T_A = 25^\circ\text{C}$, 300 μs Pulse)	V_F	1.4 1.9	Vdc
Reverse Leakage Current ($V_R = 800\text{ V}$, 300 μs Pulse Minimum, $T_A = 25^\circ\text{C}$)	I_R	2	μA
Maximum Reverse Leakage Current ($V_R = 800\text{ V}$, 300 μs Pulse Minimum, $T_A = 125^\circ\text{C}$)	I_R	50	μA
Junction Capacitance ($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_R = 10\text{ V}$)	C_J	20	pf
Reverse Recovery Time ($I_F = 500\text{mA}$, $I_R = 1\text{ A}$, $I_{RR} = 250\text{ mA}$, $T_A = 25^\circ\text{C}$)	t_{rr}	200	nsec
Reverse Energy Test (Half sine wave, $t_p = 600\text{ ns}$ @ 50% of I_P)	I_{PK}	1 (Minimum)	A



DIM	MIN	MAX	MIN	MAX
A	---	.140"	.140"	.150"
B	---	.180"	.190"	.230"
C	---	.030"	.019"	.028"
D	.97"	---	.003"	---

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RC0134B

DOCX